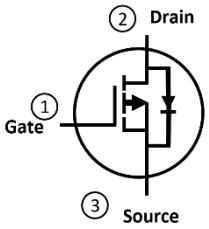
PJB120P04E-AU

40V P-Channel Enhancement Mode MOSFET

Voltage	-40 V	Current	-120 A

TO-263AB



Features

- $R_{DS(ON)}$, V_{GS}@-10V, I_D@-90A<5.2mΩ
- $R_{DS(ON)}$, V_{GS}@-4.5V, I_D@-50A<7.3mΩ
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-263AB Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 1.6924 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	±25	
Continuous Drain Current(Note 3)	T_C=25°C	I_D	-120	A
	T_C=100°C		-120	
Pulsed Drain Current(Note 1)	T_C=25°C	I_{DM}	-420	
Power Dissipation	T_C=25°C	P_D	250	W
	T_C=100°C		125	
Continuous Drain Current(Note 4)	T_A=25°C	I_D	-20	A
	T_A=70°C		-17	
Power Dissipation	T_A=25°C	P_D	3.8	W
	T_A=70°C		2.6	
Single Pulse Avalanche Current(Note 5)		I_{AS}	-23.5	A
Single Pulse Avalanche Energy(Note 5)		E_{AS}	238	mJ
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~175	°C
Thermal Resistance(Note 4)	Junction to Case	$R_{\theta JC}$	0.6	°C/W
	Junction to Ambient	$R_{\theta JA}$	40	

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250uA	-1	-1.8	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-90A	-	4.2	5.2	mΩ
		V_{GS}=-4.5V, I_D=-50A	-	5.6	7.3	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V, V_{GS}=0V	-	-	-1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±25V, V_{DS}=0V	-	-	±100	nA
Dynamic(Note 6)						
Total Gate Charge	Q_g	V_{DS}=-32V, I_D=-90A, V_{GS}=-10V	-	142	190	nC
Gate-Source Charge	Q_{gs}		-	24	-	
Gate-Drain Charge	Q_{gd}		-	37	-	
Input Capacitance	Ciss	V_{DS}=-25V, V_{GS}=0V, f=1MHz	-	7169	9400	pF
Output Capacitance	Coss		-	695	980	
Reverse Transfer Capacitance	Crss		-	541	760	
Gate resistance	R_g	f=1MHz	-	3.2	-	Ω
Turn-On Delay Time	$td_{(on)}$	V_{DS}=-32V, I_D=-90A, V_{GS}=-10V, R_G=3Ω (Note 2)	-	15	-	ns
Turn-On Rise Time	t_r		-	71	-	
Turn-Off Delay Time	$td_{(off)}$		-	114	-	
Turn-Off Fall Time	t_f		-	92	-	
Drain-Source Diode						
Diode Forward Current	I_S	T_C=25°C	-	-	-120	A
Pulsed Diode Forward Current	I_{SM}		-	-	-420	
Diode Forward Voltage	V_{SD}	I_S=-20A, V_{GS}=0V	-	-0.8	-1.3	V
Reverse Recovery Time	Trr	V_{DD}=-32V,V_{GS}=0V	-	24	-	ns
Reverse Recovery Charge	Qrr	I_S=-20A,dI_S/dt=100A/us	-	15	-	nC

NOTES :

1. Pulse width≤300us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\theta JC}$=0.6°C/W, Package limited 120A.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch^2 with 2oz.square pad of copper.
5. E_{AS} is calculated based on the condition of L=1mH, I_{AS}=-21.8A, V_{DD}=-30V, V_{GS}=-10V. 100% test at L=0.5mH, I_{AS}=-23.5A in production.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

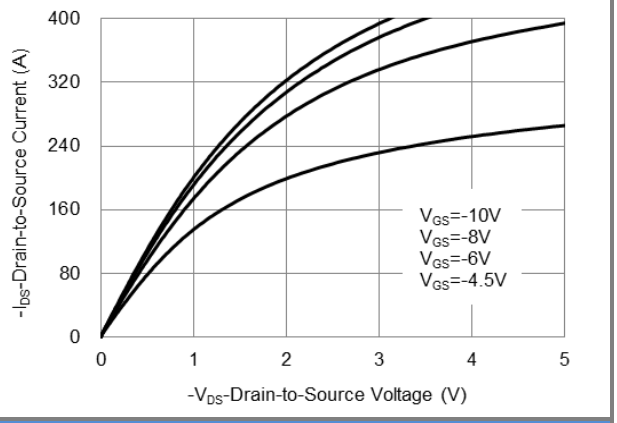

Fig.1 On-Region Characteristics

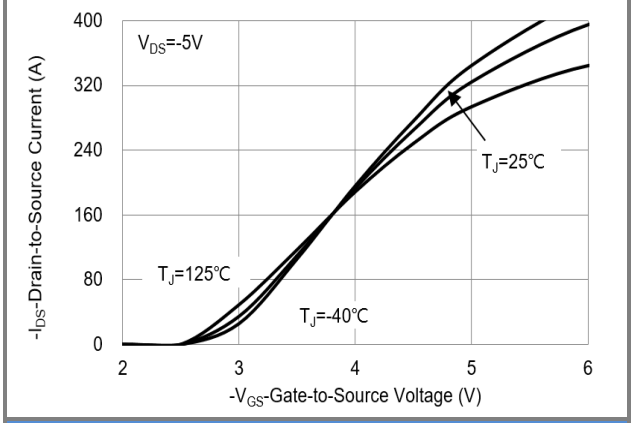

Fig.2 Transfer Characteristics

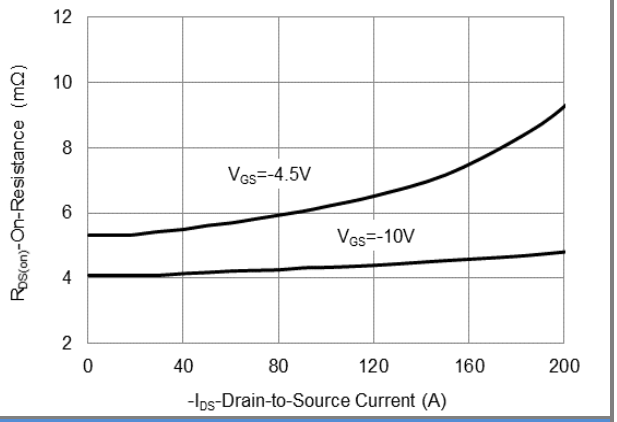

Fig.3 On-Resistance vs. Drain Current

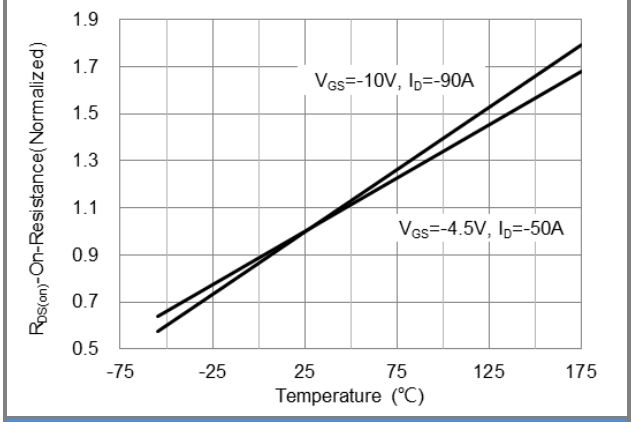

Fig.4 On-Resistance vs. Junction temperature

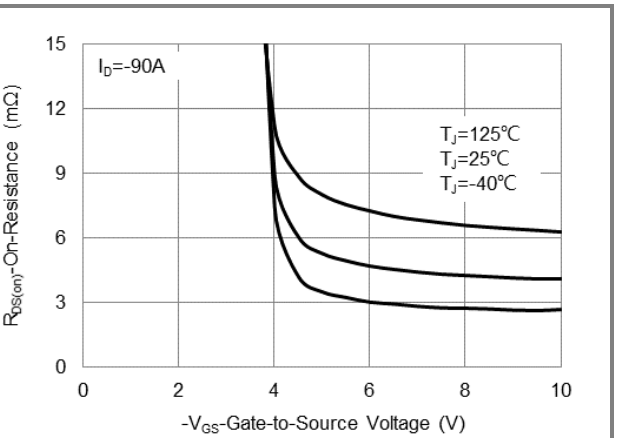

Fig.5 On-Resistance Variation with V_{GS}

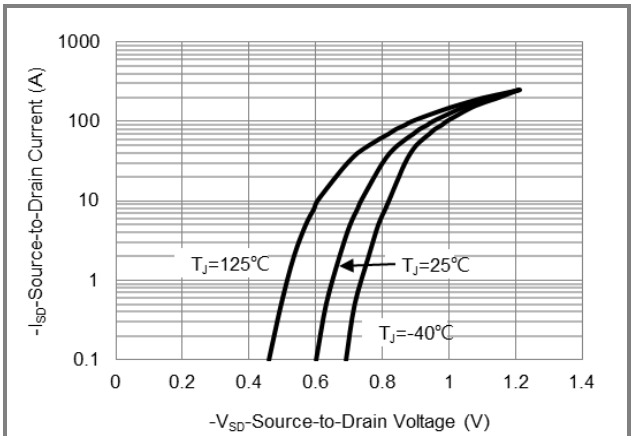

Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

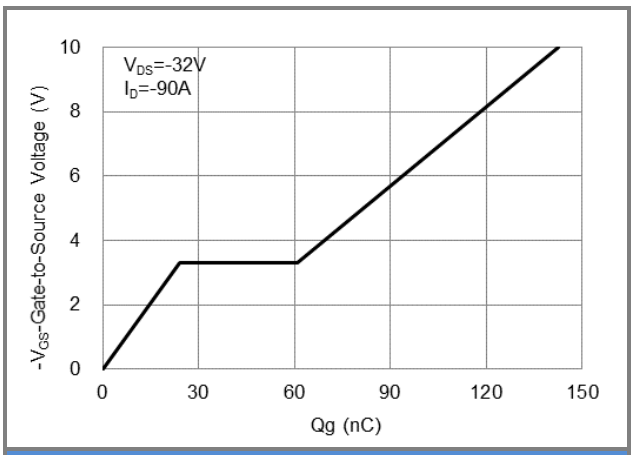

Fig.7 Gate-Charge Characteristics

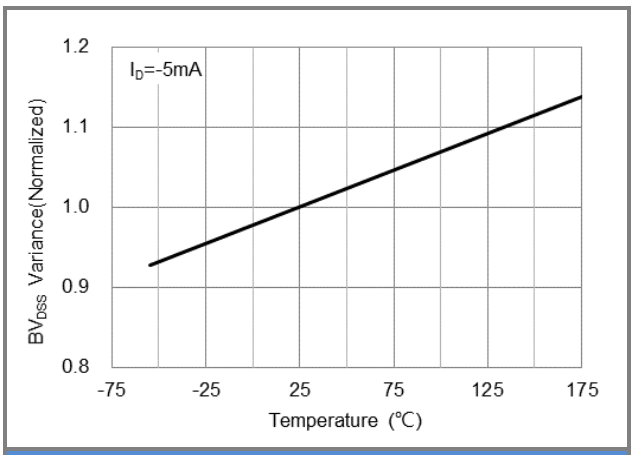

Fig.8 Breakdown Voltage Variation vs. Temperature

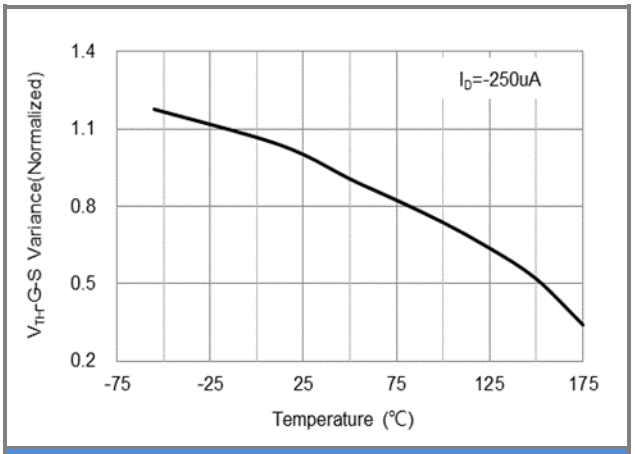

Fig.9 Threshold Voltage Variation with Temperature

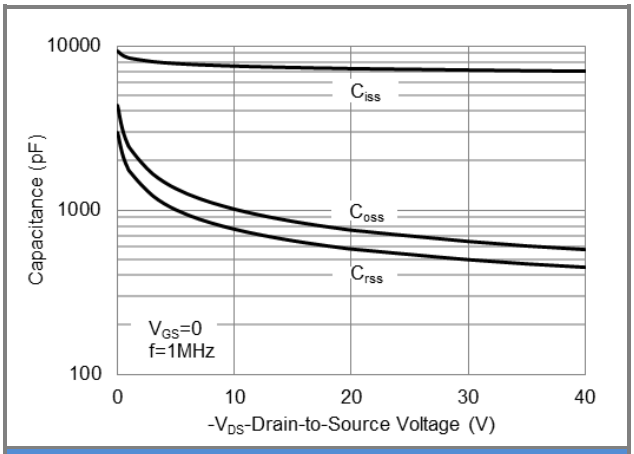

Fig.10 Capacitance vs. Drain-Source Voltage

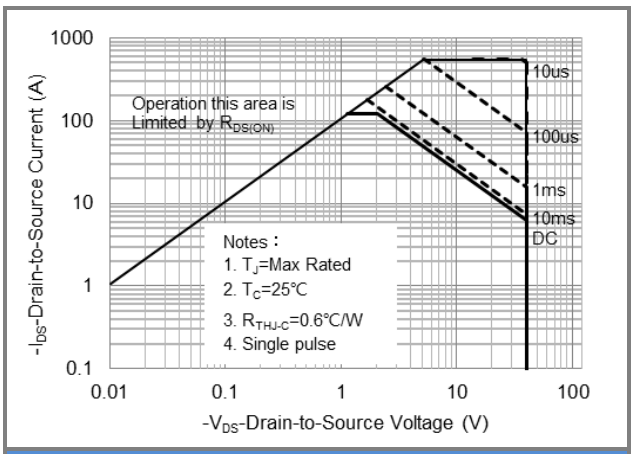

Fig.11 Maximum Safe Operating Area

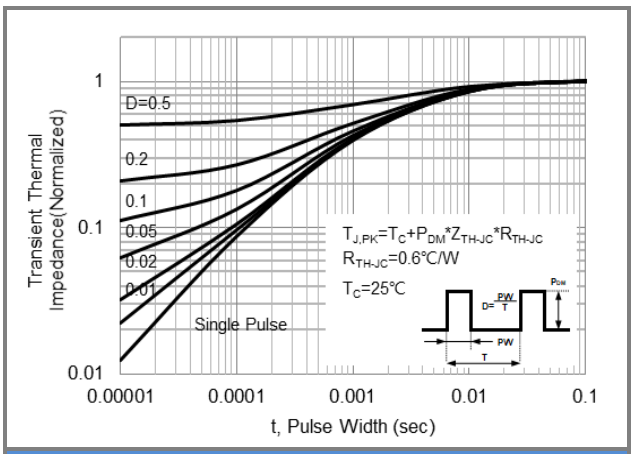

Fig.12 Normalized Transient Thermal Impedance

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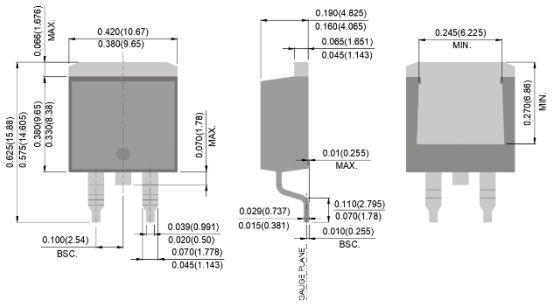
Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJB120P04E-AU	TO-263AB	800 pcs / 13” reel	120P04E

Packaging Information & Mounting Pad Layout

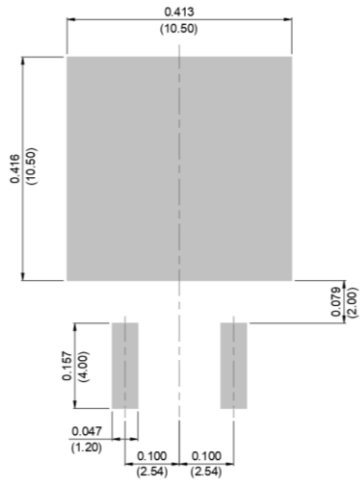
TO-263AB Dimension

Unit: inch(mm)



TO-263AB Pad Layout

Unit: inch(mm)



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